

Probing Hot Electron Flow Generated on Pt Nanoparticles with Au/TiO₂ Schottky Diodes during Catalytic CO Oxidation

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ABSTRACT

Hot electron flow generated on colloid platinum nanoparticles during exothermic catalytic carbon monoxide oxidation was directly detected with Au/TiO₂ diodes. Although Au/TiO₂ diodes are not catalytically active, platinum nanoparticles on Au/TiO₂ exhibit both chemicurrent and catalytic turnover rate. Hot electrons are generated on the surface of the metal nanoparticles and go over the Schottky energy barrier between Au and TiO₂. The continuous Au layer ensures that the metal nanoparticles are electrically connected to the device. The overall thickness of the metal assembly (nanoparticles and Au thin film) is comparable to the mean free path of hot electrons, resulting in ballistic transport through the metal. The chemicurrent and chemical reactivity of nanoparticles with citrate, hexadecylamine, hexadecylthiol, and TTAB (tetradecyltrimethylammonium bromide) capping agents were measured during catalytic CO oxidation at pressures of 100 Torr O₂ and 40 Torr CO at 373–513 K. We found that chemicurrent yield varies with each capping agent but always decreases with increasing temperature. We suggest that this inverse temperature dependence is associated with the influence of charging effects due to the organic capping layer during hot electron transport through the metal-oxide interface.

Most heterogeneous catalysts are highly dispersed metal nanoparticles supported on porous oxides.^{1–4} The phenomena associated with reduced size, such as the variation of reaction intermediates with metal nanoparticle size and shape and the role of the oxide-metal interface, are fundamental questions in catalysis. Synthesis of nanoparticles by colloid chemistry has been one of major directions to address these questions.⁵ Monodisperse platinum and rhodium nanoclusters are synthesized in solution and capped with an organic or polymer film to prevent their aggregation.^{4,6} Two dimensional nanoparticle systems have been synthesized by depositing nanoparticles on an oxide support using the Langmuir–Blodgett technique, which controls packing density. The size (1–12 nm), composition, and shape of nanoparticles are found to

be important factors influencing reaction activity and selectivity.^{4,7–9}

Atomic and molecular processes in metals can generate hot electrons with kinetic energies of 1–3 eV and mean free paths in the range of 5–10 nm.^{10,11} If the metal thickness is of the order of the electron mean free path, hot electrons can be collected during ballistic transport across the metal. Recent experimental^{11–14} and theoretical^{10,15} studies have demonstrated electronic excitations created during chemisorption and physisorption of gases at surfaces, and by chemical reactions at surfaces.^{16–18}

The oxide-metal interface is one of the major factors which determines the activity and selectivity of heterogeneous catalysts.^{19–21} It was observed that during certain reactions the oxide onto which the metal nanoparticles are deposited can dramatically change activity and selectivity even though the oxide itself is not active in catalysis.^{22,23} Earlier studies by Schwab²⁴ suggest that a Schottky barrier is formed at the oxide-metal interface and charge transport through the interface could be responsible for the enhanced catalytic reactivity. In order to elucidate these phenomena, it is

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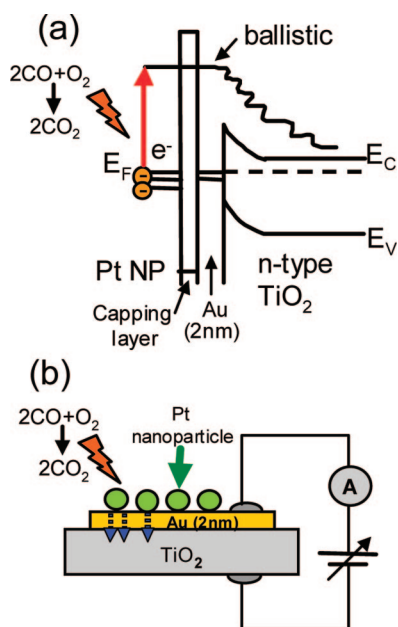


Figure 1. (a) Energy diagram and (b) schematic of hot electron generation in nanoparticles on Au/TiO₂ Schottky diode. Schottky barrier is the energy barrier between the metal and the semiconductor. The hot electrons overcome the Schottky barrier when the excess energy is larger than the barrier height and turn into low-energy electrons in the semiconductor.

important to measure hot electron transport between the nanoparticles and oxide.

In this article, we present a novel scheme for the detection of hot electrons generated on colloid nanoparticles under catalytic reaction conditions using Au/TiO₂ diodes. The nanoparticle–nanodiode hybrid system is composed of platinum nanoparticles, Au thin film (2.5 nm thick), TiO₂, and Ti/Au Ohmic contacts. The energy diagram and schematic of the nanoparticle–nanodiode hybrid system are shown in Figure 1. The interface between Au and TiO₂ forms a Schottky barrier with an energy barrier of about 1.0 eV. Hot electrons are generated on the surface of the platinum metal nanoparticles during the exothermic catalytic reaction of CO oxidation, and go over the energy barrier between Au and TiO₂. The overall thickness of the metal assembly (nanoparticles and Au thin film) is comparable to the electron mean free path, resulting in the ballistic transport of hot electrons through the metal.

Platinum colloid nanoparticles with four types of capping layer have been used; tetradecyltrimethylammonium bromide (TTAB), hexadecylamine (HDA), hexadecylthiol (HDT), and citrate. Figure 2 shows TEM images of TTAB and citrate-coated Pt nanoparticles. TTAB-capped nanoparticles were synthesized as previously reported.²⁵ Briefly, 1 mM aqueous K₂PtCl₄ in 100 mM TTAB was reduced by 30 mM NaBH₄ at 50 °C. Excess H₂ evolved from the reacting solution was released by inserting a needle into the septum. After 7 h, the reaction was allowed to cool to room temperature and left overnight to decompose the remaining NaBH₄ in water. The Pt nanoparticles were collected and washed by repeated centrifugation and sonication. TTAB-stabilized Pt nanoparticles have the shape of cubes and an average size of 12.3

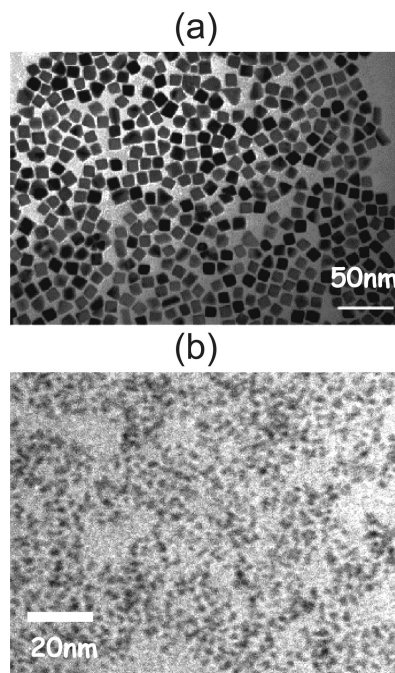


Figure 2. (a) TEM images of TTAB-capped Pt nanoparticles and (b) citrate-capped Pt nanoparticles.

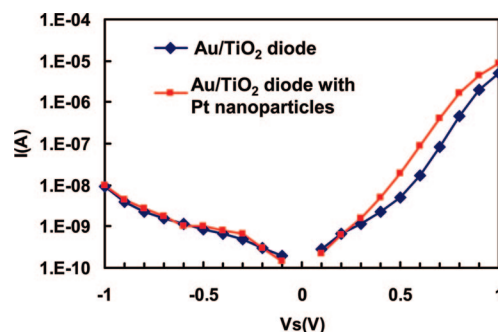


Figure 3. *I*–*V* curves of Au/TiO₂ diode before and after deposition of TTAB-capped nanoparticles.

±1.4 nm. The organic capping layer was exchanged with HDA or HDT. An 8 mL sample of TTAB-capped nanoparticles was redispersed in 2 mL of deionized water after washing, then 10 mg of HDA or 20 μL of HDT was added to the washed nanoparticles. The solution was refluxed overnight at 50 °C. Then, the residual HDA or HDT was washed with ethanol. The nanoparticles were further washed by dispersing in chloroform and precipitating with hexane. Finally, the nanoparticles were dispersed in chloroform and deposited on a diode. HDA- and HDT-capped nanoparticles had an average size of 12.3 ± 1.4 nm with cubic shapes.

Citrate-stabilized Pt nanoparticles were also prepared as previously reported.²⁶ A 20 mL sample of 1 mM K₂PtCl₄ solution was refluxed while stirring for 1 h at 110 °C, followed by the quick addition of 2 mL of 38.8 mM trisodium citrate solution. The mixture was stirred for 1 h additionally. After cooling the solution, the nanoparticle solution was centrifuged at 14 000 rpm for 30 min, followed by the dispersion of the precipitates in DI water. The citrate-stabilized Pt nanoparticles were 3.6 ± 0.5 nm in size, based on TEM images.

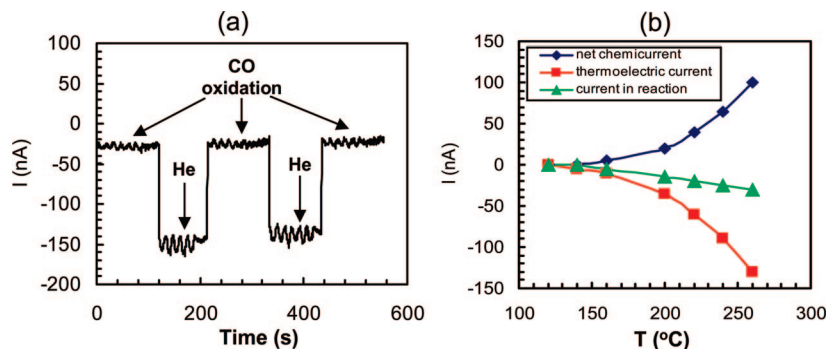


Figure 4. (a) Current measured under He (thermoelectric current) and measured in reaction conditions on citrate-capped platinum nanoparticles on Au/TiO₂ diode. (b) The net chemicurrent is derived from the difference between the thermoelectric current and reaction current.

Nanoparticles were deposited on Au/TiO₂ diodes using both drop-casting and the Langmuir–Blodgett (LB) technique.⁹ The procedures for nanoparticle deposition using LB techniques are described in Figure S1a of the Supporting Information. An SEM image of a nanoparticle array on the diode surface is shown in Figure S1b. The number of metal sites is calculated using geometrical considerations based on scanning electron microscopy (SEM) measurements of the surface area of a nanoparticle array.

Details on the fabrication of the Schottky diodes are described elsewhere.^{17,27} Vertically oriented Au/TiO₂ Schottky diodes were fabricated on an insulating p-type Si(100) wafer covered with 100 nm of thermally grown SiO₂. Reactive direct current (DC) magnetron sputtering was used to deposit approximately 150 nm titanium oxide through an aluminum shadow mask. During sputtering, bias voltage was 430 V, O₂ pressure was 11–12 sccm, and Ar pressure was 37 sccm. The film was then annealed in air at 600 °C for one hour to promote crystallization and full integration of oxygen into the oxide lattice. Next, ohmic contacts composed of 30 nm Ti and 100 nm Au were deposited onto both the TiO₂ and the insulating SiO₂. The contact on the TiO₂ provided an ohmic back contact and the contact on the SiO₂ was made to facilitate electrical connection to the thin Au Schottky contact. A 10 nm Au film was then deposited between the SiO₂ contact pad and over the edge of the bare TiO₂. This layer was thick enough to provide continuous electrical contact over the step edge of the TiO₂. Finally, a 2 nm Au pad was deposited partially on top of the 10 nm Au layer and partially on top of the bare TiO₂. The area of the 2 nm Au layer directly contacting the TiO₂ was ~1 mm². All metals were deposited using electron beam evaporation through aluminum shadow masks. Thicknesses were monitored during evaporation using a standard quartz crystal monitor. We verified that the 2 nm Au layer forms a continuous film using atomic force microscopy measurements. The rms (root-mean-square) roughness of this film is 0.4 nm.

The formation of a Schottky barrier between Au and TiO₂ has been previously reported. Tang et al. fabricated an Au/TiO₂ diode and obtained a Schottky barrier height of 0.9 eV based on thermionic emission theory.²⁸ This energy barrier is high enough to suppress the contribution of electron flow from the thermal excitation of electrons. In order to determine

barrier heights and ideality factors for the nanodiodes, we fit the I – V curves of our devices to the thermionic emission equation. For thermionic emission over the barrier, the current density of Schottky contacts as a function of applied voltage is given by²⁹

$$I = FA * T^2 \exp\left(-\frac{\Phi_n}{k_B T}\right) \cdot \left[\exp\left(\frac{e_0(V_a - R_s I)}{\eta k_B T}\right) - 1\right] \quad (1)$$

where F = area, A^* = effective Richardson constant, Φ_n = Schottky barrier height, η = ideality factor, and R_s = series resistance, respectively. Figure 3 shows the current–voltage plots of an Au/TiO₂ diode before and after deposition of TTAB-capped nanoparticles, indicating that the rectifying character of the diode remains the same. The Schottky barrier height of the diode, as obtained using the thermionic emission model,²⁹ was 1.0 eV prior to nanoparticle deposition and 0.96 eV after, indicating that nanoparticle deposition does not significantly affect the electrical properties of the system. The ideality factor increases slightly from 2.2 to 2.3 after deposition of nanoparticles.

A batch reaction system combined with electrical measurement capability was built to carry out the gas phase reaction. The design of the reaction cell has been described elsewhere.¹⁷ The reaction cell was evacuated down to 5×10^{-8} Torr by a turbo molecular pump. A ceramic heater was used to change the temperature at the sample and a type-K thermocouple was used to measure temperature at the sample surface. The temperature controller provided feedback to the current applied to the heater, which kept the fluctuations of the temperature below 0.5 °C. A sampling loop, including a gas chromatograph and a circulation pump, continuously measured reaction rates from reactant and product concentrations.

The current signal from the device was measured using a Keithley 2400 Sourcemeter at 0 V bias. Gold wires made contact to the two contact pads of the device and current generated across the Au/TiO₂ Schottky barrier by the citrate-capped Pt nanoparticles was measured both under reaction conditions and under pure He, as shown in Figure 4a. When the diode is in 1 atm He, only the thermoelectric current due to the elevated temperature is observed. This thermoelectric current is caused by the difference in electrical potential between two electrodes because of the Seebeck effect. The high thermoelectric current of the TiO₂-based diode is associated with the high Seebeck coefficient of TiO₂,

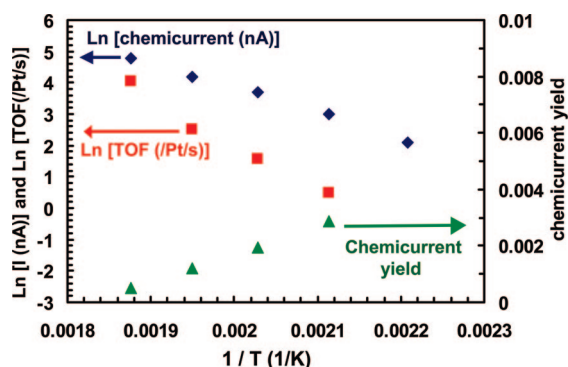


Figure 5. The plot of turnover rate, chemicurrent, and chemicurrent yield as a function of temperature measured on citrate capped Pt nanoparticles on Au/TiO₂ diode. The chemicurrent yield decreases with increasing temperature, which suggests that charging effects repel the flow of hot electrons.

which is 0.6 mV/K.³⁰ Figure 4b shows the thermoelectric current and chemicurrent measured on the nanoparticle/diode system. The difference in the currents between the thermoelectric current (760 Torr He) and reaction condition (in the mixture of reactant gases, O₂ (100 Torr), CO (40 Torr), and He (620 Torr)) is attributed to the hot electron chemicurrent generated by the CO oxidation reaction taking place at the nanoparticle surfaces. In contrast, Au/TiO₂ diodes showed no turnover rate or chemicurrent (up to 280 °C) within our detection range, as shown in the Supporting Information, which suggests that Au/TiO₂ diodes are not catalytically active.

Figure 5 shows the plot of turnover rate, chemicurrent, and chemicurrent yield measured on citrate-capped Pt nanoparticles on the Au/TiO₂ diode as a function of temperature. Interestingly, the activation energy estimated with the measurement of turnover rate is 28 kcal/mol, significantly higher than that of chemicurrent (14 kcal/mol). This big difference in activation energy is in contrast to results obtained using thin film Pt/GaN and Pt/TiO₂ diodes, which exhibited the same activation energy (20–22 kcal/mol) between the chemicurrent and turnover rate measurements.²⁷

The difference in activation energy is attributed to a charging effect occurring at the insulating capping agent layers present at the metal-oxide interface. As the hot electrons pass through the metal oxide interface, some charges can be trapped in the insulating capping layer. These trapped charges can repel the flow of other charges, reducing the total chemicurrent. This effect will be more prominent in the high current regime. As a result, the increase of chemicurrent with increasing temperature is slower than the increase in turnover rate. This causes a temperature-dependent decrease in the number of hot electrons collected per CO₂ molecule produced, or chemicurrent yield.

Another possible mechanism to explain the inverse temperature dependence of chemicurrent is a Coulomb blockade induced by hot electrons reflected back from the capping layer and equilibrated inside the nanoparticles. In this scheme, the capping layer is a barrier which electrically isolates the nanoparticles.

Table 1 shows the turnover rate and chemicurrent measured at 240 °C for nanoparticles with various capping layers on Au/TiO₂ diodes. Both turnover rate and chemicurrent were highest for the citrate-capped nanoparticles. This is most likely because the citrate is composed of only five carbon chains, which implies that reactant and product molecules can travel through the short capping layer relatively efficiently. TTAB shows intermediate activity. This is attributed to the weak bonding between TTAB and the Pt atoms in the nanoparticles, which allows the reactant and product molecules to pass through the capping layer. Hexadecylamine and hexadecylthiol, however, showed weak activity. This is because they form strong NH₂ and sulfur bonds, respectively, with Pt, which can block the reaction sites and thus lower the reaction activity. Sulfur, in particular, is well known to poison the catalytic activity of platinum surfaces during CO oxidation.^{31,32}

The chemicurrent yield of nanoparticles on Au/TiO₂ systems ranges from 3–12 × 10^{−4} electrons/CO₂ at 240 °C, which is similar to the chemicurrent yield in thin-film Pt/TiO₂ and Pt/GaN diodes of 10^{−3}–10^{−4} electrons/CO₂.¹⁸ This similarity is attributed to the comparable overall metal thicknesses of the three systems, because the travel distance of the hot electrons in the NP/Au/TiO₂ diode system (sum of the size of nanoparticle and thickness of Au layers) is comparable to the thickness of the Pt thin film (5 nm) in the Pt/GaN and Pt/TiO₂ systems. The highest chemicurrent yield was observed for citrate-stabilized Pt nanoparticles. This is partly due to the smaller size (3.5 nm) of citrate-stabilized nanoparticles, which results in a shorter travel length for the hot electrons and more efficient hot electron transport.

We also investigated possible morphological changes in the Pt nanoparticles on the Au/TiO₂ diodes after CO oxidation up to 260 °C with SEM. As shown in Figure S3a of the Supporting Information, after the reaction we did not observe any significant change in the morphology of the nanoparticles within the resolution of SEM (~1 nm), which indicates that nanoparticle agglomeration was not a factor in our measurements. The electrical character of the nanoparticle–diode system was also checked with *I*–*V* measurement before and after the reaction. Figure S3b in the Supporting Information shows the *I*–*V* plots measured on citrate-capped Pt NP on a Au/TiO₂ diode, revealing that there is no significant change in the rectifying behavior of the devices after CO oxidation. *I*–*V* curve fitting indicates

Table 1. Turnover Rate, Chemicurrent Measured at 240 °C for Nanoparticles with Various Capping Layers on Au/TiO₂ Diode; the Chemicurrent Yield Is the Number of Hot Electrons Per Product CO₂ Molecule

capping agent	citrate	TTAB	hexadecylthiol	hexadecylamine
turnover rate at 240 °C (/Pt site/s)	12.4 ± 2.3	5.3 ± 1.0	3.4 ± 0.6	3.2 ± 0.4
activation energy from turnover rate (kcal/mol)	27.3 ± 0.9	28.0 ± 1.2	27.6 ± 1.4	27.5 ± 1.0
chemicurrent at 240 °C (nA)	65 ± 6	20 ± 4	6 ± 2	5 ± 2
activation energy from chemicurrent (kcal/mol)	14.2 ± 1.5	15.4 ± 2.1	16.0 ± 3.5	15.5 ± 4.7
chemicurrent yield at 240 °C (× 10 ^{−4})	12.2 ± 3.4	8.7 ± 3.3	3.9 ± 2.0	3.5 ± 1.8

that the barrier height after the reaction is 0.95 eV, which is very similar to the diode before reaction. This measurement indicates that an efficient Schottky barrier was maintained during the chemical reaction. The overall conductance of the devices increased by a factor of 5–10 during the reaction. This increased conductance can be associated with an additional contribution to electrical transport from the partial decomposition of capping layers during CO oxidation,⁹ as well as with possible changes in the Au/TiO₂ Schottky interface associated with prolonged heating.

Due to the significant role of the capping layers in hot electron transport, it would be of great interest to study the effect of capping-layer modification and removal on chemicurrent yield. We are currently using ultraviolet exposure and oxygen plasmas to prepare exposed nanoparticles on Au/TiO₂ Schottky diodes in order to study these effects.

In conclusion, we found that Pt nanoparticles on Au/TiO₂ Schottky diodes generate hot electron current and catalytic turnover and that Au/TiO₂ alone is not catalytically active. Using nanoparticles with several different types of capping layers, we studied the influence of the capping layer on catalytic activity and chemicurrent generation. This hybrid system of nanoparticles on a Schottky diode provides us with a novel scheme for chemical sensing using metallic nanocatalysts.

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Supporting Information Available: This material is available free of charge via the Internet at <http://pubs.acs.org>.

References

- (1) Rolison, D. R. *Science* **2003**, 299 (5613), 1698–1701.
- (2) Bell, A. T. *Science* **2003**, 299 (5613), 1688–1691.
- (3) Somorjai, G. A.; Park, J. Y. *Phys. Today* **2007**, 60, 48–53.
- (4) Song, H.; Rioux, R. M.; Hoefelmeyer, J. D.; Komor, R.; Niesz, K.; Grass, M.; Yang, P. D.; Somorjai, G. A. *J. Am. Chem. Soc.* **2006**, 128 (9), 3027–3037.
- (5) Somorjai, G. A.; Tao, F.; Park, J. Y. *Top. Catal.* **2008**, 47, 1–14.
- (6) Zhang, Y.; Grass, M. E.; Habas, S. E.; Tao, F.; Zhang, T.; Yang, P.; Somorjai, G. A. *J. Phys. Chem. C* **2007**, 111, 12243–12253.
- (7) Bratlie, K. M.; Lee, H.; Komvopoulos, K.; Yang, P.; Somorjai, G. A. *Nano Lett.* **2007**, 7, 3097–3101.
- (8) Narayanan, R.; El-Sayed, M. A. *Nano Lett.* **2004**, 4 (7), 1343–1348.
- (9) Park, J. Y.; Zhang, Y.; Grass, M.; Zhang, T.; Somorjai, G. A. *Nano Lett.* **2008**, 8, 673–677.
- (10) Gadzuk, J. W. *J. Phys. Chem. B* **2002**, 106 (33), 8265–8270.
- (11) Nienhaus, H. *Surf. Sci. Rep.* **2002**, 45 (1–2), 3–78.
- (12) Huang, Y. H.; Rettner, C. T.; Auerbach, D. J.; Wodtke, A. M. *Science* **2000**, 290 (5489), 111–114.
- (13) Hellberg, L.; Stromquist, J.; Kasemo, B.; Lundqvist, B. I. *Phys. Rev. Lett.* **1995**, 74 (23), 4742–4745.
- (14) Nienhaus, H.; Bergh, H. S.; Gergen, B.; Majumdar, A.; Weinberg, W. H.; McFarland, E. W. *Phys. Rev. Lett.* **1999**, 82 (2), 446–449.
- (15) Mizielinski, M. S.; Bird, D. M.; Persson, M.; Holloway, S. J. *Chem. Phys.* **2005**, 122 (8), 084710.
- (16) Ji, X. Z.; Zupperro, A.; Gidwani, J. M.; Somorjai, G. A. *J. Am. Chem. Soc.* **2005**, 127 (16), 5792–5793.
- (17) Park, J. Y.; Somorjai, G. A. *J. Vac. Sci. Technol., B* **2006**, 24 (4), 1967–1971.
- (18) Park, J. Y.; Renzas, J. R.; Hsu, B. B.; Somorjai, G. A. *J. Phys. Chem. C* **2007**, 111 (42), 15331–15336.
- (19) Boffa, A.; Lin, C.; Bell, A. T.; Somorjai, G. A. *J. Catal.* **1994**, 149 (1), 149–158.
- (20) Hayek, K.; Fuchs, M.; Klotzer, B.; Reichl, W.; Rupprechter, G. *Top. Catal.* **2000**, 13 (1–2), 55–66.
- (21) Park, J. Y.; Renzas, J. R.; Contreras, A. M.; Somorjai, G. A. *Top. Catal.* **2007**, 46, 217.
- (22) Tauster, S. J.; Fung, S. C.; Garten, R. L. *J. Am. Chem. Soc.* **1978**, 100 (1), 170–175.
- (23) Haller, G. L.; Resasco, D. E. *Adv. Catal.* **1989**, 36, 173–235.
- (24) Schwab, G. M. *Angew. Chem., Int. Ed.* **1967**, 6 (4), 375.
- (25) Lee, H.; Habas, S. E.; Kweskin, S.; Butcher, D.; Somorjai, G. A.; Yang, P. D. *Angew. Chem., Int. Ed.* **2006**, 45 (46), 7824–7828.
- (26) Yang, J.; Lee, J. Y.; Chen, L. X.; Too, H. P. *J. Phys. Chem. B* **2005**, 109 (12), 5468–5472.
- (27) Park, J. Y.; Somorjai, G. A. *ChemPhysChem* **2006**, 7 (7), 1409–1413.
- (28) Tang, J.; White, M.; Stucky, G. D.; McFarland, E. W. *Electrochem. Commun.* **2003**, 5 (6), 497–501.
- (29) Using Richardson constant for TiO₂, $A = 24 \text{ A/cm}^2 \text{ K}^2$.
- (30) He, Q. Y.; Hao, Q.; Chen, G.; Poudel, B.; Wang, X. W.; Wang, D. Z.; Ren, Z. F. *Appl. Phys. Lett.* **2007**, 91, (5).
- (31) Bonzel, H. P.; Ku, R. *J. Chem. Phys.* **1973**, 59 (4), 1641–1651.
- (32) Bartholomew, C. H.; Agrawal, P. K.; Katzer, J. R. *Adv. Catal.* **1982**, 31, 135–242.

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